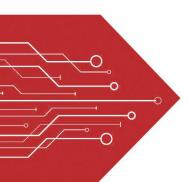
## MSKSEMI















**ESD** 

TVS

TSS

MOV

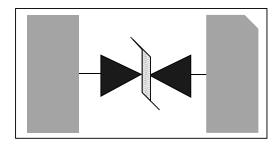
GDT

**PLED** 

# Broduct data sheet







**SLP1006P2T** 

## Schematic & PIN Configuration

## **Features**

- 100Watts peak pulse power (tp =  $8/20\mu$ s)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.25pF typ.)
- Protection one data/power line to:
- IEC 61000-4-2  $\pm$  20kV contact  $\pm$ 20kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20μs)

## **Applications**

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

#### **Mechanical Data**

- SLP1006P2T
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## **Absolute Maximum Rating**

Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>p</sub> =8/20μs )	P <sub>PP</sub>	100	Watts
Peak Pulse Current ( t <sub>p</sub> =8/20μs ) (note1)	$I_{pp}$	4.0	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$ m V_{ESD}$	20 20	kV
Lead Soldering Temperature	$T_{ m L}$	260(10seconds)	$^{\circ}$
Junction Temperature	$T_{\mathrm{J}}$	-55 to + 125	°C
Storage Temperature	$T_{\rm stg}$	-55 to + 125	°C

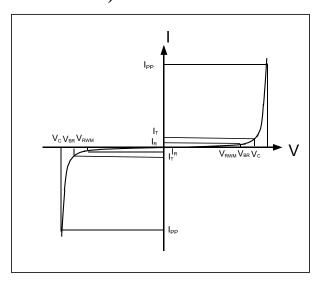


## **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6.0			V
Reverse Leakage Current	$I_R$	V <sub>RWM</sub> =5V,T=25°C			100	nA
Peak Pulse Current	$I_{PP}$	tp =8/20μs			4.0	A
Clamping Voltage	$V_{\rm C}$	I <sub>PP</sub> =4A,t <sub>p</sub> =8/20μs			25	V
Junction Capacitance	Cj	$V_R = 0V, f = 1MHz$		0.25	0.5	pF

## Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter	
Ірр	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ Ipp	
V <sub>RWM</sub>	Working Peak Reverse Voltage	
Ir	Maximum Reverse Leakage Current @ VRWM	
V <sub>BR</sub>	Breakdown Voltage @ IT	
Iτ	Test Current	



Note:.  $8/20\mu s$  pulse waveform.



## **Typical Characteristics**

Figure 1: Peak Pulse Power vs. Pulse Time

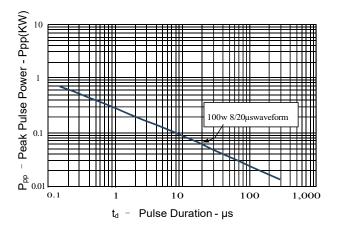


Figure3: Pulse Waveform

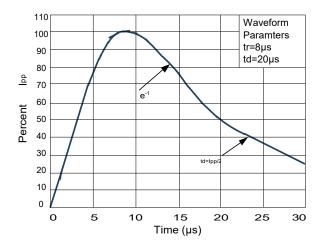
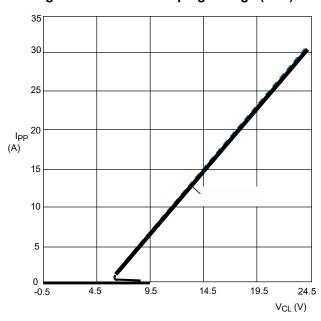


Figure5: Positive Clamping voltage (TLP)



**Figure 2: Power Derating Curve** 

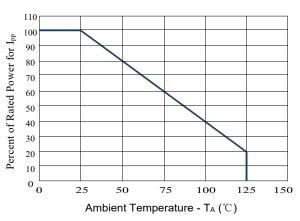


Figure 4: Clamping Voltage vs.lpp

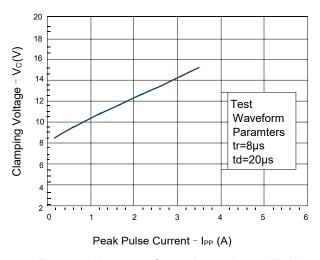
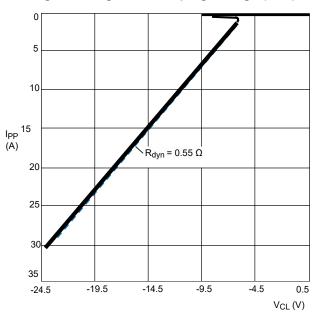


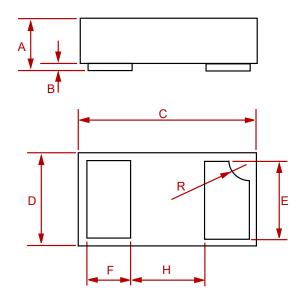
Figure 5: Negative Clamping voltage (TLP)





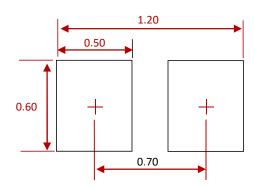


#### **PACKAGE MECHANICAL DATA**



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
Α	0.0125	0.02	0.32	0.52
В	0.000	0.002	0.00	0.05
С	0.037	0.043	0.95	1.080
D	0.022	0.027	0.55	0.680
E	0.016	0.024	0.40	0.60
F	0.008	0.012	0.20	0.30
Н	0.015Typ.		0.40Тур.	
R	0.001	0.005	0.05	0.15

## **Suggested Pad Layout**



### NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

## **REEL SPECIFICATION**

P/N	PKG	QTY
RCLAMP0531T.TCT-MS	SLP1006P2T	3000



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